

In the Claims:

Please cancel claims 1-3 without prejudice or disclaimer of the subject matter contained therein.

Please add claims 6-10 as follows:

*add
as*

*Sub
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--6. A semiconductor device comprising:

- a gate formed on an active region of a substrate;
- a field oxide formed on the substrate adjacent the active region;
- a protective layer formed on a said field oxide, said protective layer being a material different than said field oxide;
- an insulating layer formed on the substrate including said gate, said field oxide and said protective layer;
- a contact hole formed through said insulating layer; and
- a connecting wire coupled to said gate through said contact hole.

7. The semiconductor device of claim 6, wherein said protective layer is a polysilicon layer.

8. The semiconductor device of claim 6, wherein said protective layer is formed on said field oxide only.

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9. The semiconductor device of claim 6, wherein said gate is a MOSFET gate.